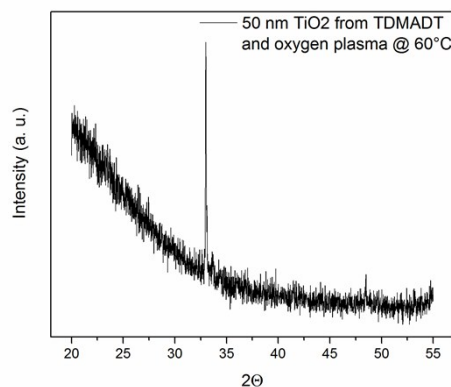


Supplementary Information



SI Fig. 1: Representative XRD pattern of a 50 nm TiO₂ thin film on Si(100), deposited at 60 °C using TDMADT and oxygen plasma (150 ms, 200 W).